



Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	4.5	kV
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**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	35	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
$I_H$	$I_T=500mA$		MAX.	35	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	800	V/ $\mu s$
(dI/dt)c	(dV/dt)c=20V/ $\mu s$ $T_j=125$		MIN.	10	A/ms
$t_{on}$	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	$\mu s$
$t_{off}$				30	

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=17A t_p=380\mu s$	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.77	V
$R_D$	Dynamic resistance	$T_j=125$	35	m
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	$\mu A$
$I_{RRM}$		$T_j=125$	0.5	mA

**THERMAL RESISTANCES**

**Symbol**

**Param9 0 Td [(P)1 (ar)3 (am)15.7DC .0 (ar)3 (ar /P <</MCID 1334.**

**JST12E-800CW**



**FIG.7:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

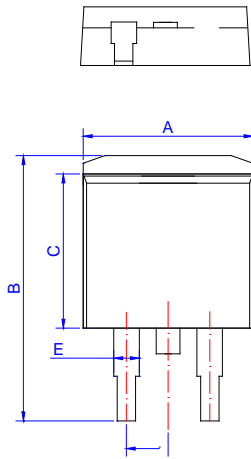




**JST12E-800CW**

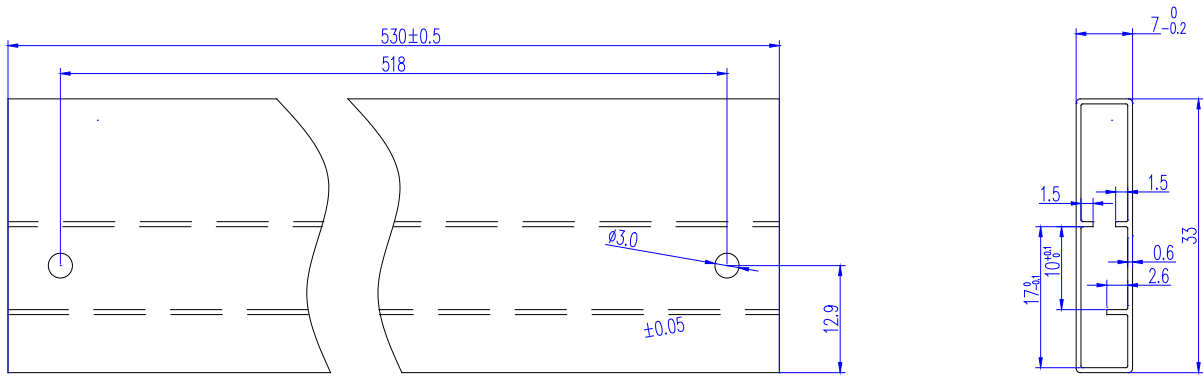
**JieJie Microelectronics Co., Ltd.**

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

DELIVERY MODE



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